

SEMICONDUCTOR TECHNICAL DATA

BC546/7/8

EPITAXIAL PLANAR NPN TRANSISTOR

GENERAL PURPOSE APPLICATION. SWITCHING APPLICATION .

FEATURES

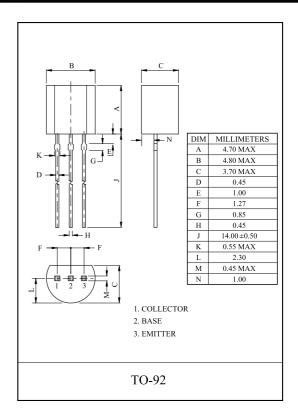
 \cdot High Voltage : BC546 V_{CEO} =65V.

 \cdot For Complementary With PNP Type BC556/557/558.

MAXIMUM RATING (Ta=25)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
	BC546		80	V	
Collector-Base Voltage	BC547	V_{CBO}	50		
	BC548		30		
Collector-Emitter Voltage	BC546		65	V	
	BC547	$ m V_{CEO}$	45		
	BC548		30		
Emitter-Base Voltage	BC546	$ m V_{EBO}$	6		
	BC547		6	V	
	BC548		5		
Collector Current	BC546	I_{C}	100		
	BC547		100	mA	
	BC548		100		
Base Current	BC546	I_{B}	20	mA	
	BC547		20		
	BC548		20		
Emitter Current	BC546	${ m I_E}$	-100	mA	
	BC547		-100		
	BC548		-100		
Callastan Bayyan Diin-ti		*P _C	625	mW	
Collector Power Dissipation)11	, r _C	400	III VV	
Junction Temperature		T _j	150		
Storage Temperature Range		T_{stg}	-55 150		

*Cu Lead-Frame : 625mW Fe Lead-Frame : 400mW



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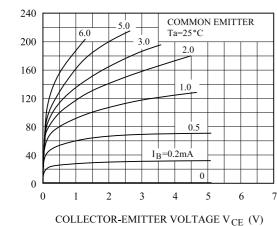
ELECTRICAL CHARACTERISTICS (Ta=25)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB}=30V, I_{E}=0$	-	-	15	nA
DC Current Gain (Note)	BC546		V_{CE} =5V, I_{C} =2mA	110	-	450	
	BC547	h_{FE}		110	-	800	
	BC548			110	-	800	
Collector-Emitter Saturation Voltage		V _{CE(sat)}	$I_C=100$ mA, $I_B=5$ mA	-	-	0.6	V
Base-Emitter Saturation Voltage		V _{BE(sat)}	I _C =100mA, I _B =5mA	-	0.9	1.1	V
Base-Emitter Voltage		V _{BE(ON)} 1	V _{CE} =5V, I _C =2mA	0.58	-	0.7	V
		V _{BE(ON)} 2	V_{CE} =5V, I_{C} =10mA	-	-	0.75	V
Transition Frequency		f_T	V _{CE} =5V, I _C =10mA, f=100MHz	-	150	-	MHz
Collector Output Capacitance		C _{ob}	V_{CB} =10V, f=1MHz, I_{E} =0	-	-	4.5	pF
Noise Figure		NF	V_{CE} =6V, I_{C} =0.1mA R_{g} =10k , f=1kHz	-	1.0	10	dB

NOTE : According to the value of h_{FE} the BC546, BC547, BC548 are classified as follows.

CLASSIFIC	CATION	none	A	В	С
	BC546	110 450	110 220	200 450	-
$h_{ m FE}$	BC547	110 800	110 220	200 450	420 800
	BC548	110 800	110 220	200 450	420 800

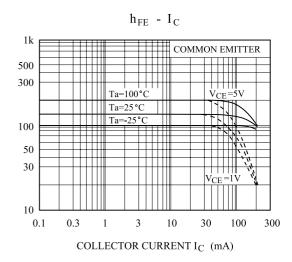
 I_{C} - V_{CE} (LOW VOLTAGE REGION)



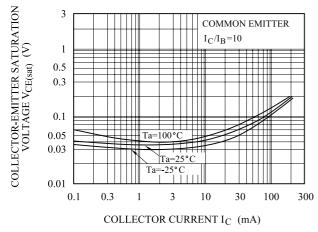
COLLECTOR CURRENT IC (mA)

DC CURRENT GAIN h_{FE}

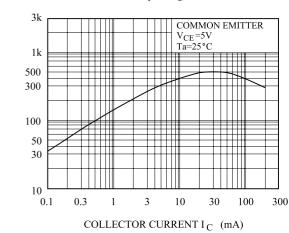
TRANSITION FREQUENCY f_T (MHz)



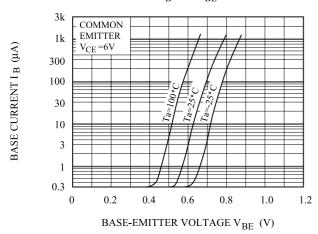
 $V_{\text{CE(sat)}}\,$ - $\,I_{\,\text{C}}$







 I_B - V_{BE}



P_C - Ta

